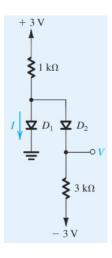
Assignment #2, Total: 10 pts

Name: NetID:

## **Chapter 4. Diodes**

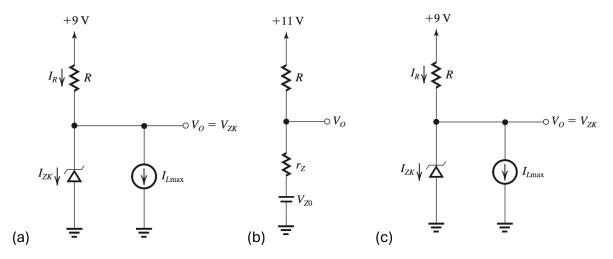
1. (0.5 pts) Assuming that the diodes in the circuits are *ideal*, find the values of the labeled voltage and current.



2. (2 pts) Design a zener regulator circuit using a 7.5-V zener specified at 10 mA. The zener has an incremental resistance  $r_z = 30~\Omega$  and a knee current of 0.5 mA. The

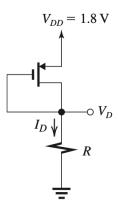
regulator operates from a 10-V supply and delivers a nominal current of 5 mA to the load.

- (a) What is the value of R you have chosen?
- (b) What is the output voltage when both the supply is 10% high and the load is removed?
- (c) What is the largest load current that can be delivered while the zener operates at a current no lower than the knee current while the supply is 10% low?



## **Chapter 5. MOS Field-Effect Transistors (MOSFETs)**

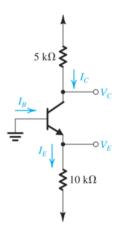
3. (1 pt) The PMOS transistor in the circuit has  $V_t = -0.5$  V,  $\mu_p C_{ox} = 100 \,\mu\text{A/V}^2$ , L = 0.18  $\mu\text{m}$ , and  $\lambda$  = 0. Find the values required for W and R in order to establish a drain current of 160  $\mu\text{A}$  and a voltage  $V_D$  of 0.8 V.



4. (1 pt) For a particular MOSFET operating in the saturation region at a constant  $v_{GS}$ ,  $i_D$  is found to be 200  $\mu$ A for  $v_{DS}$  = 1 V and 205  $\mu$ A for  $v_{DS}$  = 1.5 V. Find the values of  $r_o$ ,  $V_A$ , and  $\lambda$ .

## **Chapter 6. Bipolar Junction Transistors (BJTs)**

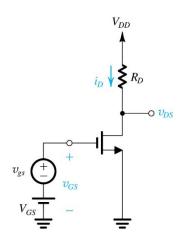
5. (1 pt) In the circuit shown in the figure, the power supplies are  $\pm 3$  V and the voltage at the emitter was measured and found to be -0.7 V. If  $\beta$  = 50, find I<sub>E</sub>, I<sub>B</sub>, I<sub>C</sub>, and V<sub>C</sub>.



## **Chapter 7. Transistor Amplifiers**

6. (1 pt) A designer wants to create a BJT amplifier with a gm of 20 mA/V and a base input resistance of 4000  $\Omega$  or more. What collector-bias current should she choose? What is the minimum  $\beta$  she can tolerate for the transistor used?

- 7. (1.5 pt) Consider the amplifier of the following circuit:  $V_{DD}$  = 5 V,  $R_D$  = 24 k $\Omega$ , (W/L) = 1 mA/V<sup>2</sup>, and V<sub>t</sub> = 1 V.
  - (a) Find the coordinates of the two end points of the saturation-region segment of the amplifier transfer characteristic, that is, points A and B.
  - (b) If the amplifier is biased to operate with an overdrive voltage  $V_{\text{OV}}$  of 0.5 V, find the coordinates of the bias point Q on the transfer characteristic. Also, find the value of  $I_{\text{D}}$  and of the incremental gain  $A_{\text{v}}$  at the bias point.



- 8. (2 pts) The following figure shows a discrete-circuit amplifier. The input signal  $v_{sig}$  is coupled to the gate through a very large capacitor (shown as infinite). The transistor source is connected to ground at signal frequencies via a very large capacitor (shown as infinite). The output voltage signal that develops at the drain is coupled to a load resistance via a very large capacitor (shown as infinite). All capacitors behave as short circuits for signals and as open circuits for dc.
  - (a) If the transistor has  $V_t = 1$  V, and  $k_n = 4$  mA/V<sup>2</sup>, verify that the bias circuit establishes  $V_{GS} = 1.5$  V,  $I_D = 0.5$  mA, and  $V_D = +7.0$  V. That is, assume these values, and verify that they are consistent with the values of the circuit components and the device parameters.
  - (b) Find gm and  $r_o$  if  $V_A = 100$  V.
  - (c) Find  $R_{in}$ ,  $v_{gs}/v_{sig}$ ,  $v_o/v_{gs}$ , and  $v_o/v_{sig}$ .

